

# IND/MED/MIL



Complete Memory Solutions for the Industrial Market



Over 80% of ISSI's business is in markets such as Automotive, Industrial and Communication Infrastructure, where customers demand high quality product with long life cycles. Our company strategy is based around the requirements of these customers. By offering long term support and high quality on ALL of our products, we reduce the total cost for our customers.

#### DRAM PRODUCT LINE

- Long-term support for all ISSI DRAMs: 7-10 years typical
- Provide complete portfolio of DRAM's (SDR, DDR, DDR2, DDR3, DDR4, mSDR, mDDR, LPDDR2)
- Long-term roadmaps on all 3.3V SDRAM in all densities up to 512Mb, including x32 products
- Mobile DRAM families for power sensitive applications
- EDO/FP Asynchronous DRAM
- Com. (0°C to +70°C), Ind. (-40°C to +85°C) and Auto. (-40°C to +85°C/+105°C/+115°C) temperature grade options
- Copper lead-frame TSOP for enhanced reliability in demanding environments
- · Both Lead-free (RoHS) and Leaded BGA support
- · Known Good Die (KGD) solutions

#### SRAM PRODUCT LINE

- Long-term support for all ISSI SRAMs: 7-10 years typical
- Legacy Asynchronous SRAMs:
   64Kb-8Mb, including 5V options
- High Speed Asynchronous SRAMs:
   1Mb-16Mb, x8, x16, x32 options, (1Mb-8Mb with ECC)
- Low Power Asynchronous SRAMs: 1Mb-16Mb, Ultra-Low Power
- Pseudo SRAMs: 4Mb-64Mb, PSRAM and CRAM options
- Synchronous SRAMs:
   Up to 72Mb, with QUAD SRAM/DDRII options, [4Mb with ECC]
- Ind. (-40°C to +85°C) and Auto. (-40°C to +125°C) temperatures
- Provide wafer level (die) solutions

DRAM	4M	16M	32M	64M	128M	256M	512M	1G	2G	4G	8G
3.3V, 5V EDO/FP											
3.3V SDRAM					•		•				
2.5V DDR					•	•	•				
1.8V DDR2											
1.35V & 1.5V DDR3/DDR3L								•	•	•	•
1.2V (2.5V) DDR4											
Mobile DRAM											
1.8V/2.5V/3.3V Mo- bile SDRAM			•	•	•	•	•				
1.8V Mobile DDR											
1.2V (1.8V) LPDDR2											
1.2V (1.8V) LPDDR3									•	•	

Industrial/Automotive Temperature, Long Term Support, Leaded/Lead Free

STATUS ■ Production ■ Roadmap ■ Under Consideration

STATUS

Production

Asynchronous SRAMs	64K	256K	512K	1M	2M	зм	4M	8M	16M	32M	64M
5V			•				•				
High Speed Asynchronous		•	•	ECC	ECC	•	ECC	ECC	•		
Ultra Low Power											
Pseudo SRAMS										•	
High Speed Memory	2M	4M	8M	16M	36M	72M	144M	288M	576M	1G	2G
Standard/No-Wait(ZBT) Synchronous	•	■ ECC	•	•	•	•					
QUAD (Compatible to QDR-II™)				٠	•	٠					
DDRII				•	•	•					
QUADP/DDRIIP (Compatible to QDR-II+™)				٠	٠	٠					
RLDRAM2										•	
RLDRAM3									•		•
Industrial/Automotive Temperature, Long Term Support, Leaded/Lead Free											

■ Under Consideration

Roadmap

## ► FLASH PRODUCT LINE

· Industry Standard

Serial and Parallel Flash

• Densities: 256K - 256Mb

Interface

Serial: SPI, Dual/Quad SPI, Multi-I/O SPI, QPI, DTR-SPI

Parallel: FWH/ISA/x29GL Page-mode

Voltage: 3V, 2.5V, 1.8V

Serial Flash	256K	512K	1M	2M	4M	8M	16M	32M	64M	128M	256M	512M	1G
2.5/3V	•	•		•	•	•		•			-	•	
1.8V									•	•	•		
Parallel Flash (ISA)	512K	1M	4M	32M	64M	128M	256M	512M	1G				
3V Uniform Block				*1									
3V IS29GL- Series Page Mode					*1,*2	*2	*2	-	•				
1.8V IS29GL- Series Page Mode					•	•		•					
SLC NAND	1G	2G	4G	8G									
3V x8 and x16 options	*3	*3	*3	*4									
1.8V x8 and x16 options	*3	*3	*3	*4									
Industrial/Automotive Temperature, Long Term Support, Leaded/Lead Free													
STATUS Production Roadmap Under Consideration *1 - Top/Bottom, *2 - High/Low, *3 - 1 or 4 bit ECC, *4 - 4bit ECC													

### **CONTACT INFORMATION:**

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